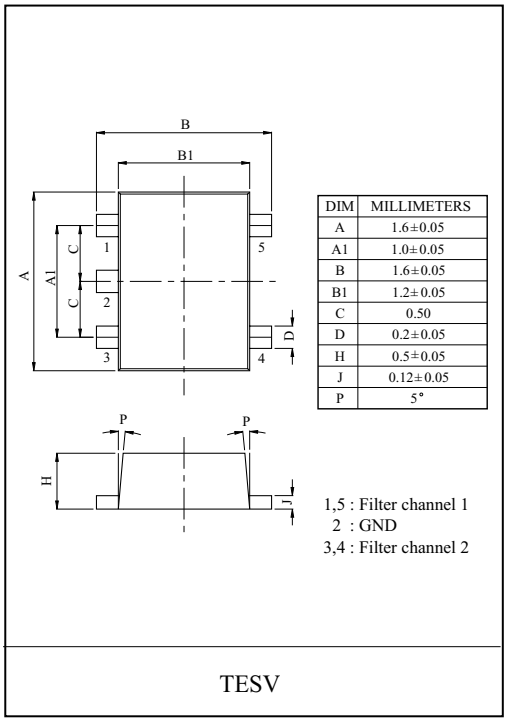
For EMI Filtering and ESD Protection.



DIM	MILLIMETERS
A	1.6±0.05
A1	1.0±0.05
B	1.6±0.05
B1	1.2±0.05
C	0.50
D	0.2±0.05
H	0.5±0.05
J	0.12±0.05
P	5°

TESV

FEATURES

- EMI/RFI filtering.
- ESD Protection to IEC 61000-4-2 Level 4.
- Low insertion loss.
- Good attenuation of high frequency signals.
- Low clamping voltage.
- Low operating and leakage current.

APPLICATIONS

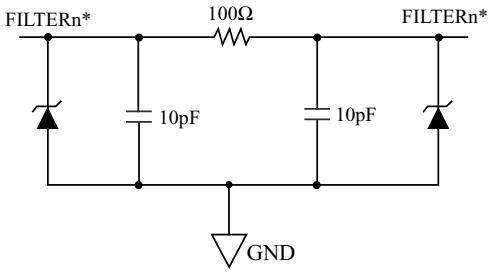
- Cell phone handsets.
- RF communications equipment.

MAXIMUM RATING (Ta=25℃)

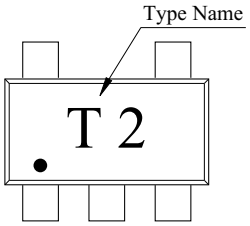
CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Power Per Resistor	P_R	100	mW
Power Dissipation	*P_D	200	
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 ~ 150	℃

* Total Package Power Dissipation

EQUIVALENT CIRCUIT



MARKING

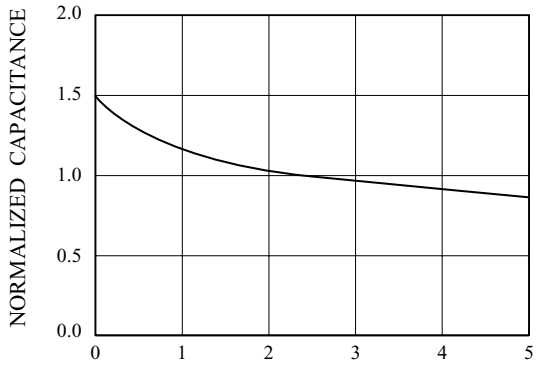


ELECTRICAL CHARACTERISTICS (Ta=25℃)

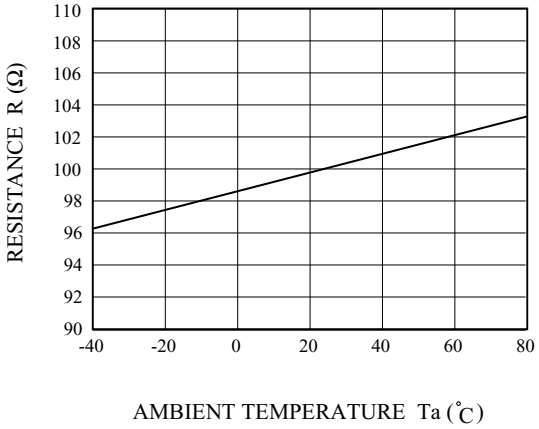
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	I_t=1mA	6	-	-	V
Reverse Leakage Current	I_R	V_{RWM}=3V	-	-	0.1	μA
Cutoff Frequency	f_{3dB}	V_R=0V, Z_{SOURCE}=50 Ω, Z_{LOAD}=50 Ω	-	150	-	MHz
Attenuation	$\|S_{21}\|^2$	V_R=0V, f = 800MHz~3GHz, Z_{SOURCE}=50 Ω, Z_{LOAD}=50 Ω	25	-	-	dB
Resistance	R	Between Input and Output	-	100	-	Ω
Capacitance	C	V_R=2.5V, Between I/O Pins and GND	-	20	-	pF

Downloaded from Elcodis.com electronic components distributor

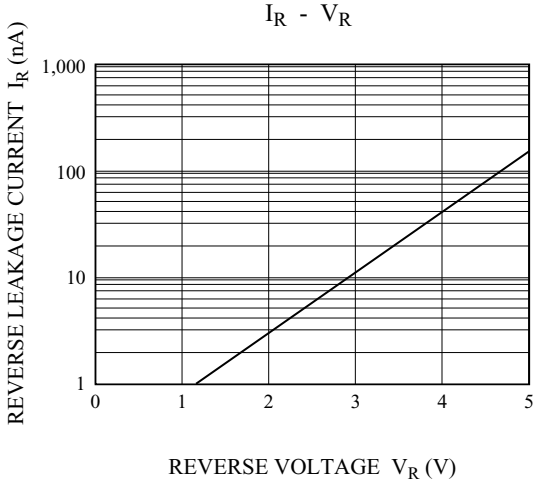
C_J - V_R



R - Ta



I_R - V_R



Downloaded from Elcodis.com electronic components distributor